

UTC UNISONIC TECHNOLOGIES CO., LTD

UT03P06 POWER MOSFET Preliminary

-0.3A, -60V P-CHANNEL **POWER MOSFET**

DESCRIPTION

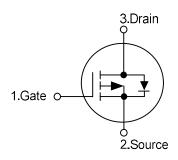
The UTC UT03P06 is a P-channel MOS Field Effect Transistor, it uses UTC's advanced technology to provide the customers with high switching speed and a minimum on-state resistance.

The UTC UT03P06 is suitable for high voltage switching applications.

FEATURES

- * $R_{DS(ON)} \le 4.5 \Omega$ @ V_{GS} =-10V, I_D =-0.15A $R_{DS(ON)} \le 6.5 \Omega @ V_{GS} = -4.5V, I_D = -0.15A$
- * High switching speed
- * Low input capacitance

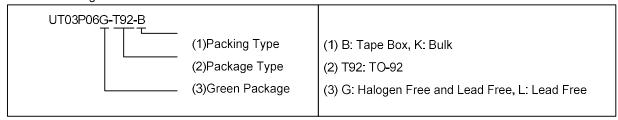
SYMBOL



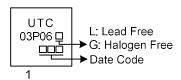
ORDERING INFORMATION

Ordering Number		Daakana	Pin	Daakina			
Lead Free	Halogen Free	Package	1	2	3	Packing	
UT03P06L-T92-B	UT03P06G-T92-B	TO-92	S	G	D	Tape Box	
UT03P06L-T92-K	UT03P06G-T92-K	TO-92	S	G	D	Bulk	

Note: Pin Assignment: G: Gate S: Source D: Drain



MARKING



1 TO-92

www.unisonic.com.tw 1 of 5

■ **ABSOLUTE MAXIMUM RATING** (T_C=25°C unless otherwise specified)

PARAME	TER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	-60	V
Gate-Source Voltage		V _{GSS}	±20	V
Dunin Cumant	DC	I _D	-0.3	Α
Drain Current	Pulsed (Note 2)	I _{DM}	-0.6	Α
Power Dissipation (T _A =25°C)		P _D	700	mW
Junction Temperature		TJ	+150	°C
Storage Temperature Range		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	178.6	°C/W

■ **ELECTRICAL CHARACTERISTICS** (T_J=25°C unless otherwise specified)

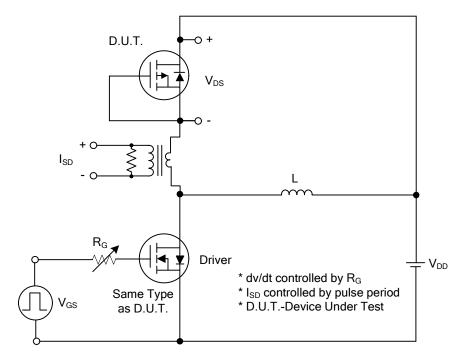
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS					•		
Drain-Source Breakdown Voltag	е	BV _{DSS}	V _{GS} =0V, I _D =-250μA				V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =-60V, V _{GS} =0V			-1	μΑ
0-1- 0	Forward	,	V _{GS} =+20V, V _{DS} =0V			+10	μΑ
Gate-Source Leakage Current	Reverse	I_{GSS}	V _{GS} =-20V, V _{DS} =0V			-10	μΑ
ON CHARACTERISTICS	ON CHARACTERISTICS						
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	-1.0		-3.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =-10V, I _D =-0.15A			4.5	Ω
			V _{GS} =-4.5V, I _D =-0.15A			6.5	Ω
DYNAMIC CHARACTERISTICS	3						
Input Capacitance	Input Capacitance				23.3		pF
Output Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =-25V, f=1.0MHz		8.7		pF
Reverse Transfer Capacitance		C_{RSS}			3.3		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	\		6.1		nC
Gate to Source Charge		Q_GS	V_{DS} =-48V, V_{GS} =-10V, I_{D} =-0.3A, I_{D} =-1mA (Note 1, 2)		1.8		nC
Gate to Drain Charge		Q_GD	ID IIIA (Note 1, 2)		0.9		nC
Turn-ON Delay Time		t _{D(ON)}			3.4		ns
Rise Time		t_R	V _{DS} =-30V, V _{GS} =-10V, I _D =-0.3A,		16		ns
Turn-OFF Delay Time		t _{D(OFF)}	R _G =25Ω (Note 1, 2)		6.4		ns
Fall-Time		t_{F}			20		ns
SOURCE-DRAIN DIODE RATIN	NGS AND	CHARACTERI	ISTICS				
Maximum Continuous Drain-Source Diode		_				-0.3	Α
Forward Current		I _S				-0.3	А
Maximum Pulsed Drain-Source Diode		I _{SM}				-0.6	Α
Forward Current						-0.0	^
Diode Forward Voltage		V_{SD}	I _F =-0.3A, V _{GS} =0V			-1.4	V

Notes: 1. Pulse Test: Pulse width \leq 300 μ s, Duty cycle \leq 2%.

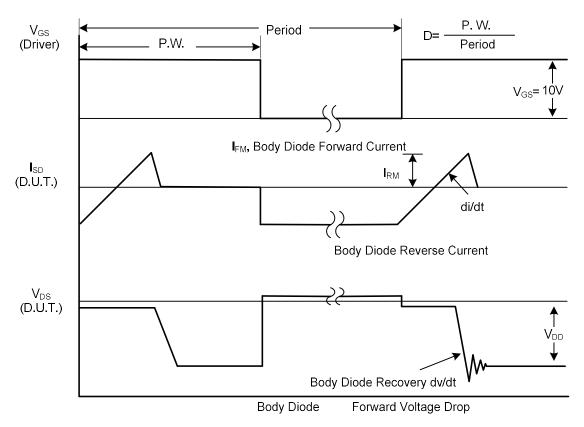
^{2.} Repetitive Rating: Pulse width limited by maximum junction temperature

^{2.} Essentially independent of operating temperature.

TEST CIRCUITS AND WAVEFORMS

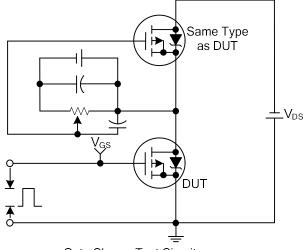


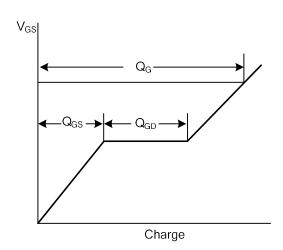
Peak Diode Recovery dv/dt Test Circuit



Peak Diode Recovery dv/dt Waveforms

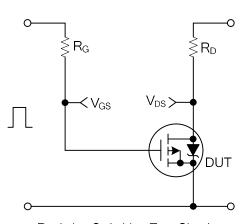
■ TEST CIRCUITS AND WAVEFORMS



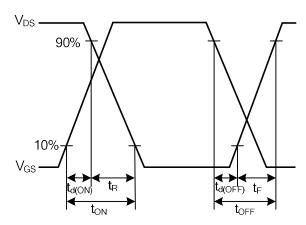


Gate Charge Test Circuit

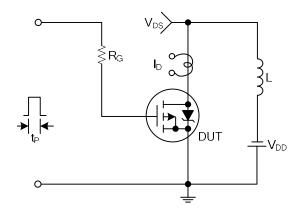




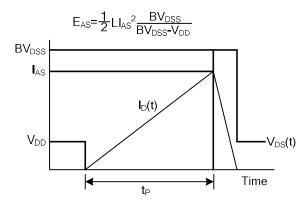
Resistive Switching Test Circuit



Resistive Switching Waveforms



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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